FAIRCHILD SEMICONDUCTOR®

April 2007

UniFET™

FDP12N35 / FDPF12N35
350V N-Channel MOSFET

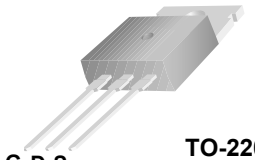
Features

- 12A, 350V, $R_{DS(on)}$ = 0.38Ω @V_{GS} = 10 V
- Low gate charge (typical 18 nC)
- Low Crss (typical 15 pF)
- Fast switching
- Improved dv/dt capability

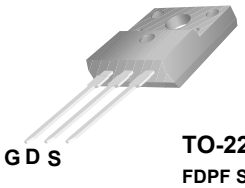
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

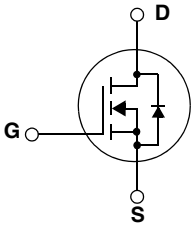
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.



TO-220
FDP Series



TO-220F
FDPF Series



Absolute Maximum Ratings

Symbol	Parameter		FDP12N35	FDPF12N35	Unit
V_{DSS}	Drain-Source Voltage		350		V
I_D	Drain Current	- Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	12 7.2	12* 7.2*	A A
I_{DM}	Drain Current	- Pulsed (Note 1)	48	48*	A
V_{GSS}	Gate-Source voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	335		mJ
I_{AR}	Avalanche Current	(Note 1)	12		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	13.5		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P_D	Power Dissipation	(T_C = 25°C) - Derate above 25°C	135 1.09	31.3 0.25	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300		°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP12N35	FDPF12N35	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.92	4.0	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP12N35	FDP12N35	TO-220	-	-	50
FDPF12N35	FDPF12N35	TO-220F	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25°C	350	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	--	0.35	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 350V, V_{GS} = 0V V_{DS} = 280V, T_C = 125°C	-- --	-- --	1 10	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 6A	--	0.32	0.38	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40V, I_D = 6A (Note 4)	--	13	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	--	855	1110	pF
C_{oss}	Output Capacitance		--	135	175	pF
C_{rss}	Reverse Transfer Capacitance		--	15	25	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 175V, I_D = 12A R_G = 25Ω	--	30	70	ns
t_r	Turn-On Rise Time		--	180	370	ns
$t_{d(off)}$	Turn-Off Delay Time		--	35	80	ns
t_f	Turn-Off Fall Time	(Note 4, 5)	--	60	130	ns
Q_g	Total Gate Charge	V_{DS} = 280V, I_D = 12A V_{GS} = 10V	--	18	25	nC
Q_{gs}	Gate-Source Charge		--	5	--	nC
Q_{gd}	Gate-Drain Charge	(Note 4, 5)	--	8	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	12	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	48	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 12A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 12A dI_F/dt =100A/μs (Note 4)	--	270	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.3	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 4mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 12A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

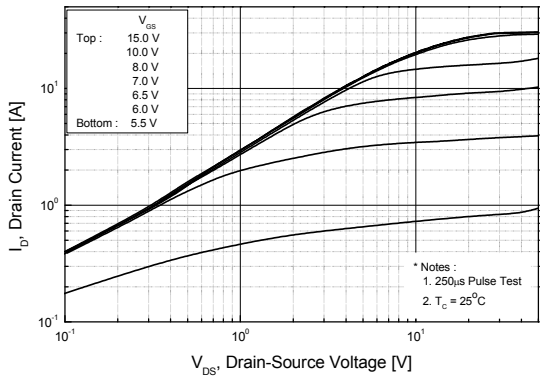


Figure 2. Transfer Characteristics

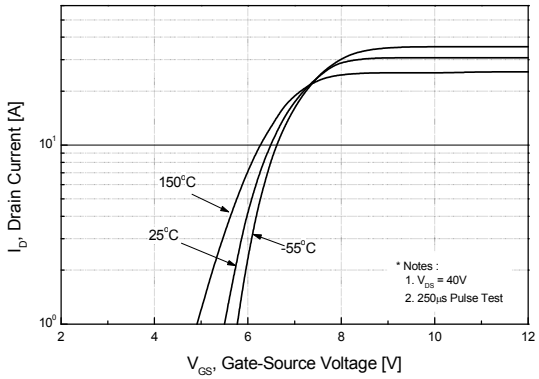


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

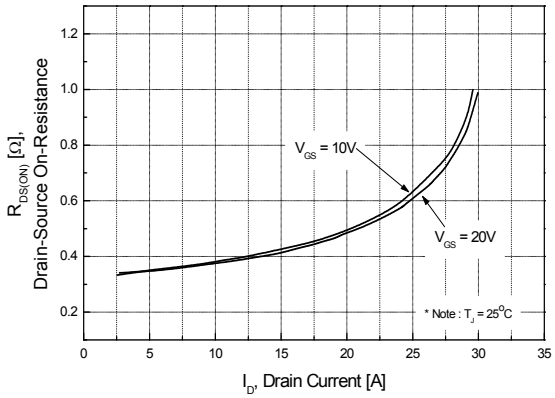


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

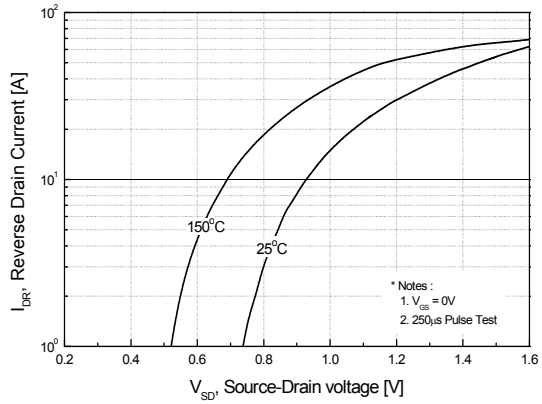


Figure 5. Capacitance Characteristics

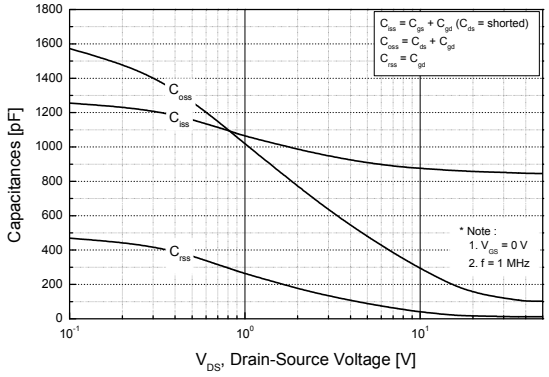
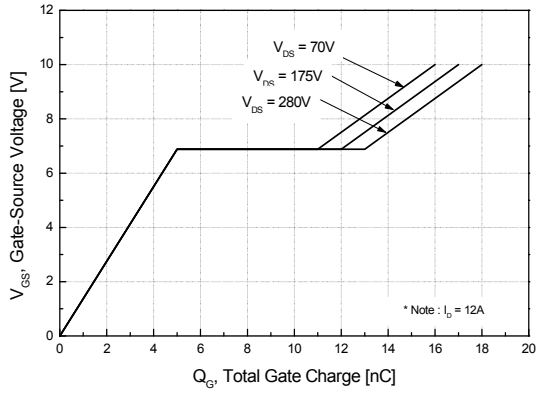


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

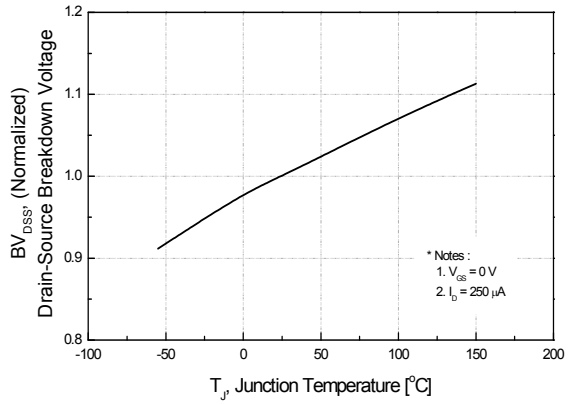


Figure 8. On-Resistance Variation vs. Temperature

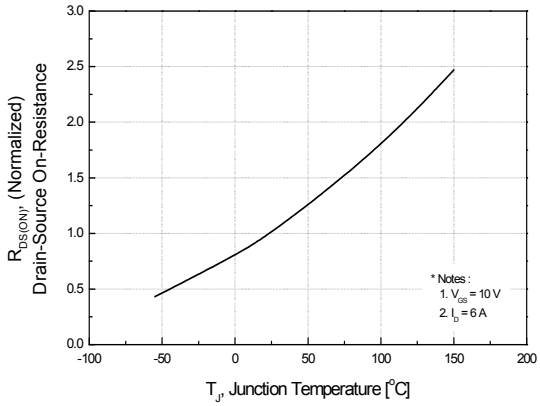


Figure 9-1. Maximum Safe Operating Area for FDP12N35

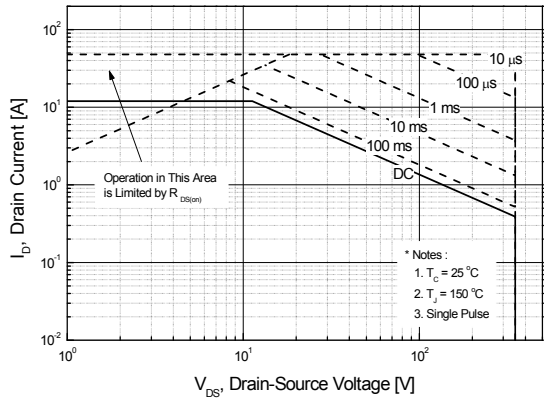


Figure 9-2. Maximum Safe Operating Area for FDPF12N35

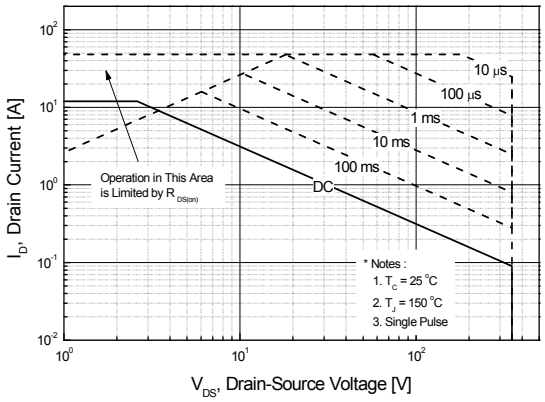
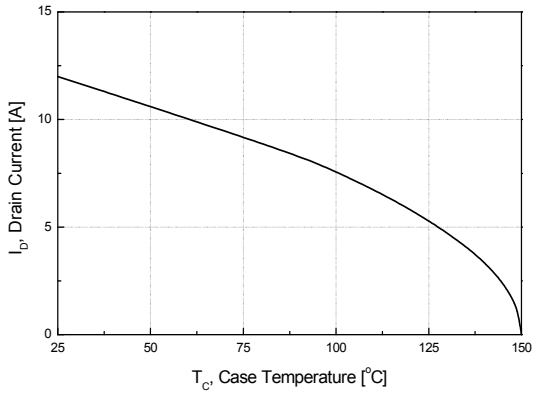


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve for FDP12N35

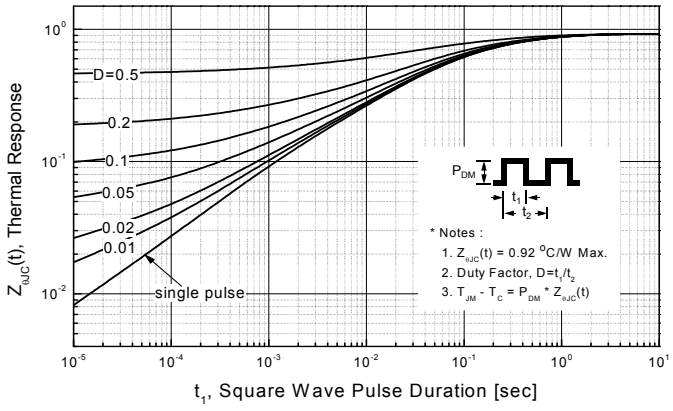
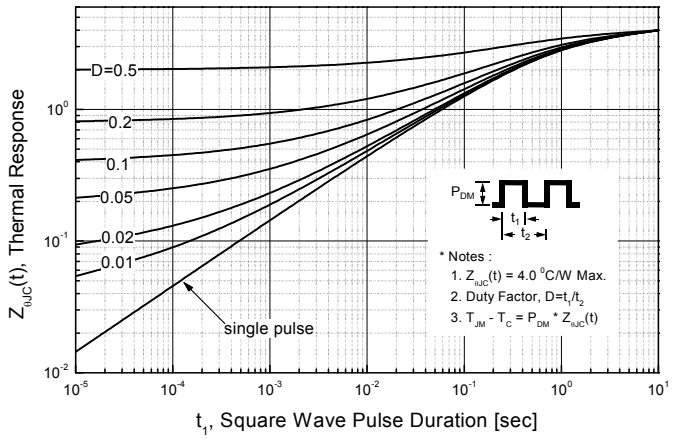
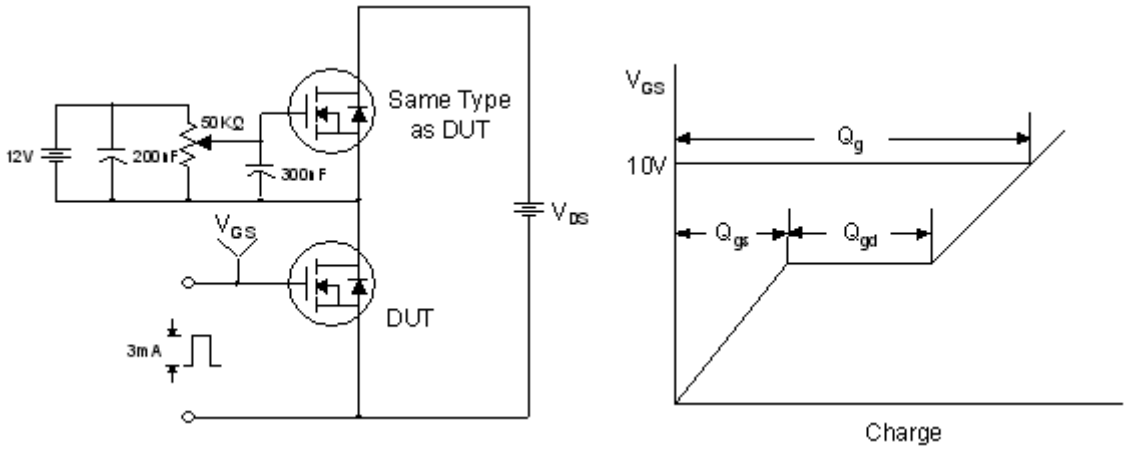


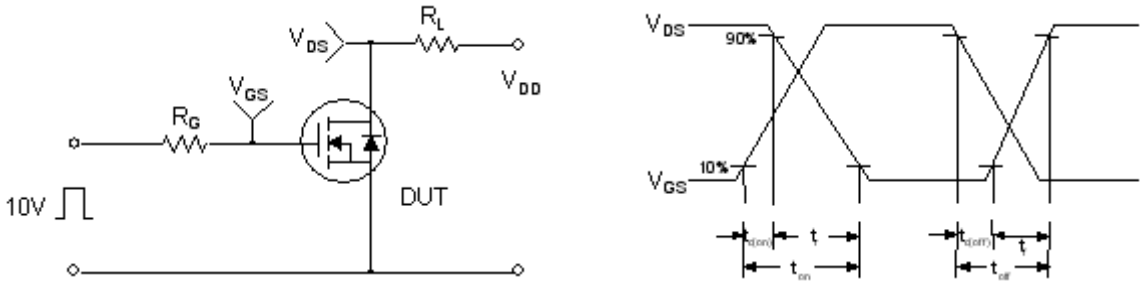
Figure 11-2. Transient Thermal Response Curve for FDPF12N35



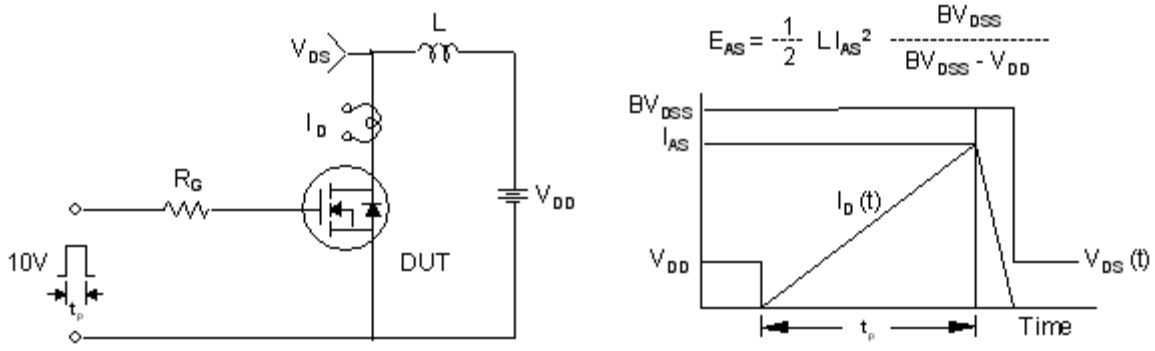
Gate Charge Test Circuit & Waveform



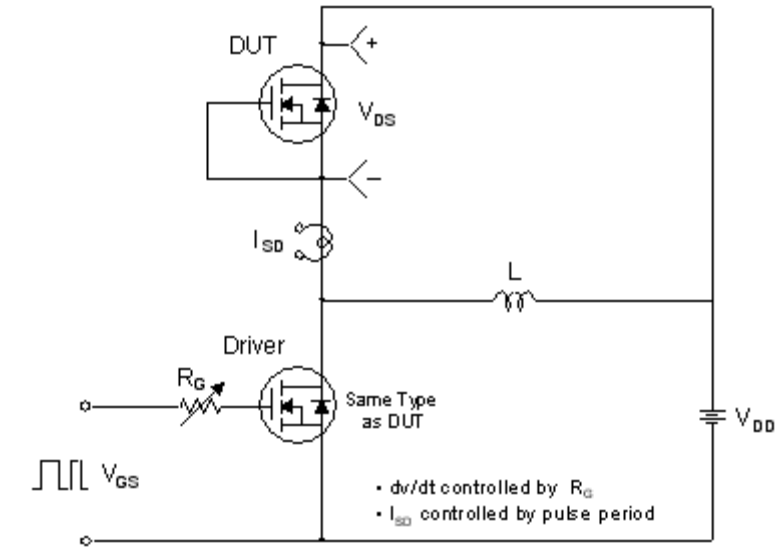
Resistive Switching Test Circuit & Waveforms

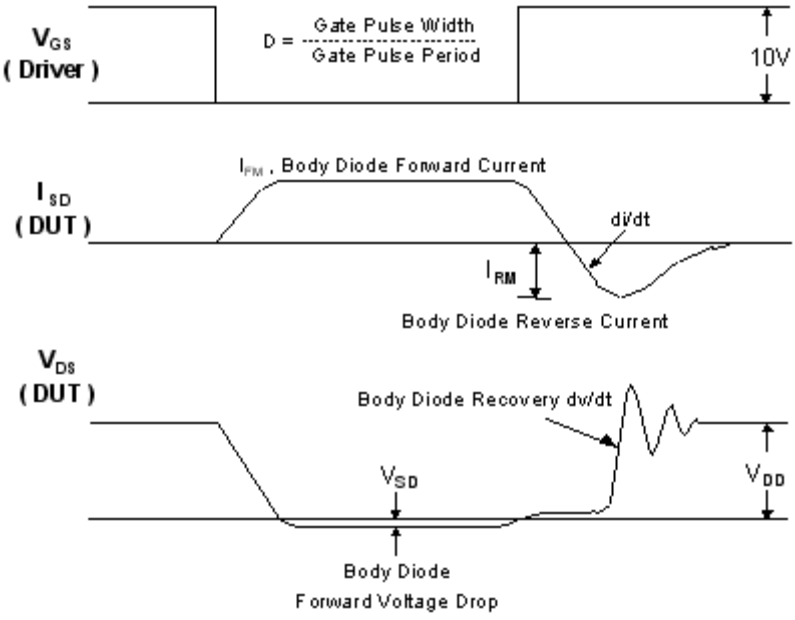


Unclamped Inductive Switching Test Circuit & Waveforms



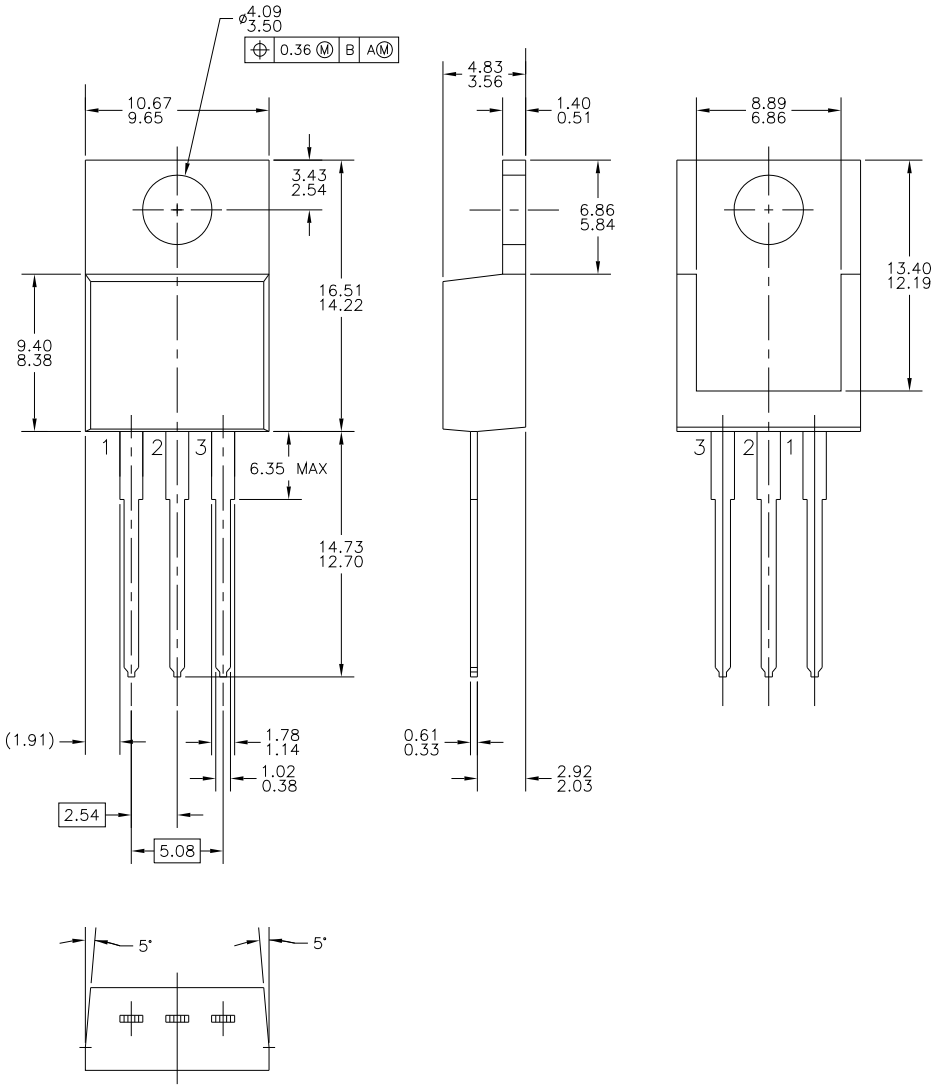
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

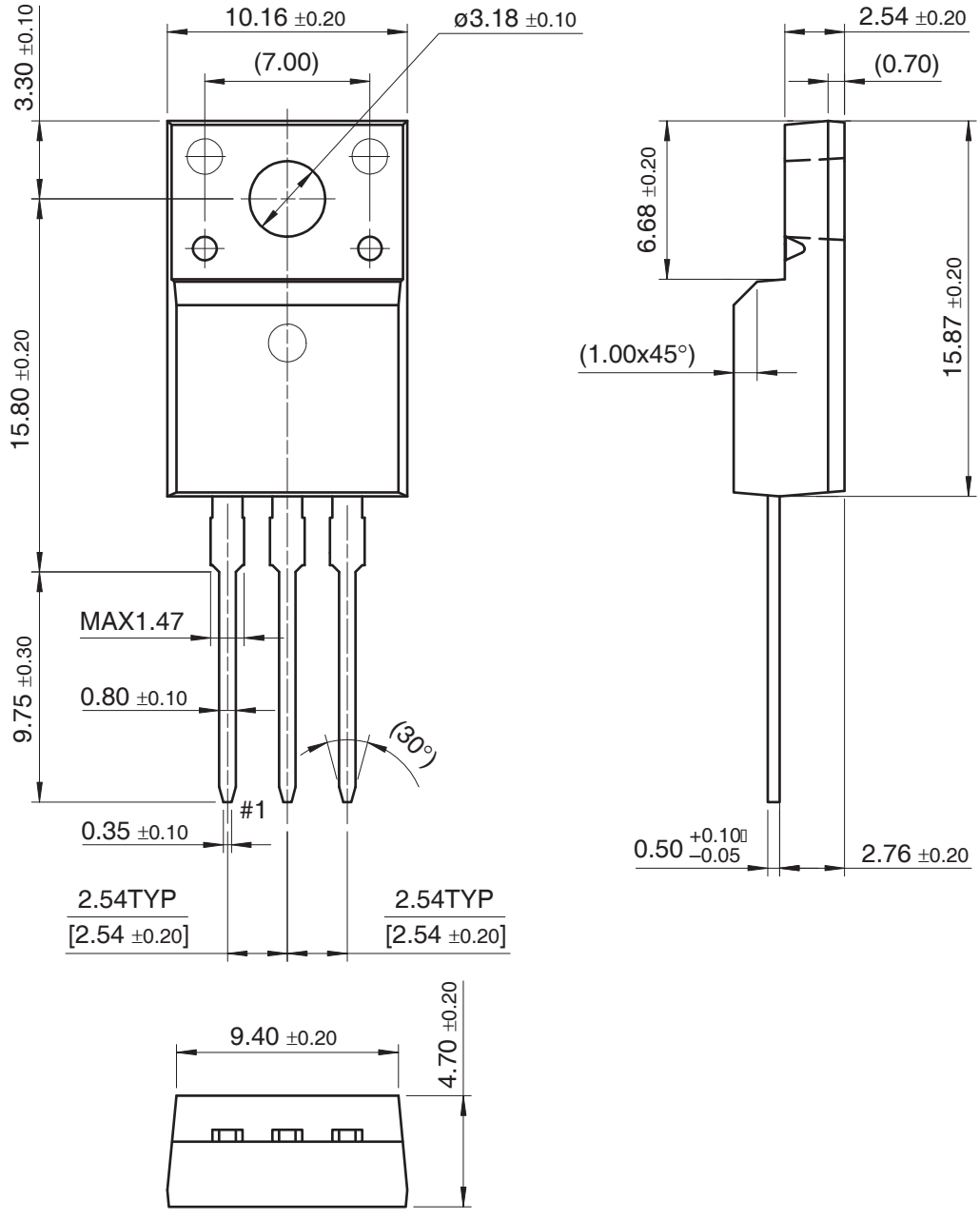
TO-220



Dimensions in Millimeters

Mechanical Dimensions (Continued)

TO-220F



Dimensions in Millimeters

FAIRCHILD
SEMICONDUCTOR®

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx®
Across the board. Around the world.™
ActiveArray™
Bottomless™
Build it Now™
CoolFET™
CROSSVOLT™
CTL™
Current Transfer Logic™
DOME™
E²CMOS™
EcoSPARK®
EnSigna™
FACT Quiet Series™
FACT®
FAST®
FASTr™
FPS™
FRFET®
GlobalOptoisolator™
GTO™
HiSeC™
i-Lo™
ImpliedDisconnect™
IntelliMAX™
ISOPLANAR™
MICROCOUPLER™
MicroPak™
MICROWIRE™
Motion-SPM™
MSX™
MSXPro™
OCX™
OCXPro™
OPTOLOGIC®
OPTOPLANAR®
PACMAN™
PDP-SPM™
POP™
Power220®
Power247®
PowerEdge™
PowerSaver™
Power-SPM™
PowerTrench®
Programmable Active Droop™
QFET®
QS™
QT Optoelectronics™
Quiet Series™
RapidConfigure™
RapidConnect™
ScalarPump™
SMART START™
SPM®
STEALTH™
SuperFET™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SyncFET™
TCM™
The Power Franchise®
™
TinyBoost™
TinyBuck™
TinyLogic®
TINYOPTO™
TinyPower™
TinyWire™
TruTranslation™
µSerDes™
UHC®
UniFET™
VCX™
Wire™

PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor.The datasheet is printed for reference information only.

Rev. I26